IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A cleaning method for a vapor phase deposition apparatus for forming film on a substrate, comprising:

inserting the substrate into a chamber;

introducing a film forming gas into [[a]] the chamber via a shower head;

forming a film on the substrate with the shower head at a first temperature;

removing the substrate from the chamber;

activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves;

introducing the cleaning gas into the chamber;

raising the temperature of the shower head to a second temperature greater than the first temperature; and then

removing a deposit comprising tungsten and silicon.

2. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises restricting a supply of a cooling medium to the shower head.

3. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 2, wherein raising the temperature of the shower head further comprises heating the shower head by a heater.

4. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein raising the temperature of the shower head comprises heating the shower head by a heater.

5. (Previously Presented) A cleaning method for a vapor phase deposition apparatus according to claim 1, wherein the temperature of the shower head is raised to about 50°C or above.

6. (Currently Amended) A cleaning method for a vapor phase deposition apparatus for forming film on a substrate, comprising:

inserting the substrate into a chamber;

introducing a film forming gas into [[a]] the chamber via a shower head wherein the film forming gas comprises a compound containing tungsten atoms;

forming a film on the substrate with the shower head at a first temperature;

removing the substrate from the chamber;

activating a cleaning gas including a compound containing fluorine atoms by exposure to microwaves;

introducing the cleaning gas into a chamber;

raising the temperature of the shower head to a second temperature greater than the first temperature, wherein the temperature of the shower head is raised to about 70°C or above; and then

removing a deposit comprising tungsten and silicon.

7-13. (Canceled)